TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74VHC03F, TC74VHC03FN, TC74VHC03FT

# QUAD 2-INPUT NAND GATE (OPEN DRAIN)

The TC74VHC03 is an advanced high speed CMOS 2-INPUT NAND GATE fabricated with silicon gate  $C^2MOS$  technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

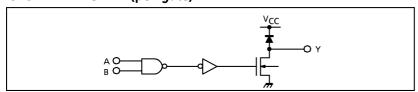
Pin configuration and function are the same as the TC74VHC00. But the TC74VHC03 has, as its outputs, high performance MOS N-channel transistors. (OPEN-DRAIN outputs) This device can, therefore, with a suitable pull-up resistors, be used in wired-AND, LED driver and other application.

An input protection circuit ensures that 0 to 5.5V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

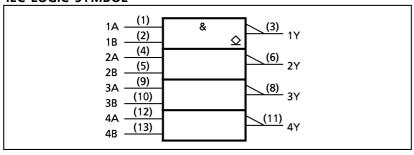
### FEATURES:

- High Speed······ $t_{pZ}$  = 3.7ns(typ.) at  $V_{CC}$  = 5V
- Low Power Dissipation ·············  $I_{CC} = 2\mu A(Max.)$  at  $Ta = 25^{\circ}C$
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Power Down Protection is provided on all inputs.
- Wide Operating Voltage Range ···· V<sub>CC</sub> (opr) = 2V ~ 5.5V
- Low Noise .....V<sub>OLP</sub> = 0.8V (Max.)
- Pin and Function Compatible with 74ALS03

#### SYSTEM DIAGRAM (per gate)

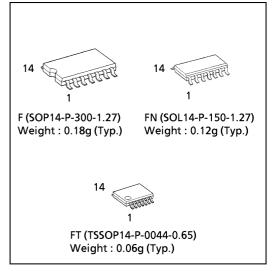


### **IEC LOGIC SYMBOL**

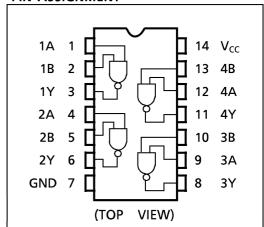


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(Note) The JEDEC SOP (FN) is not available in Japan.



### **PIN ASSIGNMENT**



### TRUTH TABLE

| Α | В | Υ |
|---|---|---|
| L | L | Z |
| L | Н | Z |
| Н | L | Z |
| Н | Н | L |

# **ABSOLUTE MAXIMUM RATINGS**

| PARAMETER                          | SYMBOL                | VALUE                    | UNIT |
|------------------------------------|-----------------------|--------------------------|------|
| Supply Voltage Range               | $V_{CC}$              | <b>−</b> 0.5~7.0         | V    |
| DC Input Voltage                   | V <sub>IN</sub>       | <b>−</b> 0.5~7.0         | V    |
| DC Output Voltage                  | V <sub>OUT</sub>      | $-0.5 \sim V_{CC} + 0.5$ | V    |
| Input Diode Current                | I <sub>IK</sub>       | <b>-20</b>               | mA   |
| Output Diode Current               | I <sub>OK</sub>       | ± 20                     | mA   |
| DC Output Current                  | I <sub>OUT</sub>      | 25                       | mA   |
| DC V <sub>CC</sub> /Ground Current | I <sub>cc</sub>       | ± 50                     | mΑ   |
| Power Dissipation                  | <b>P</b> <sub>D</sub> | 180                      | mW   |
| Storage Temperature                | T <sub>stg</sub>      | <b>−65~150</b>           | °C   |

# **RECOMMENDED OPERATING CONDITIONS**

| PARAMETER                | SYMBOL           | VALUE   | UNIT     |
|--------------------------|------------------|---|----------|
| Supply Voltage           | $V_{CC}$         | 2.0~5.5   | <        |
| Input Voltage            | VIN              | 0~5.5   | <b>V</b> |
| Output Voltage           | V <sub>OUT</sub> | 0~V <sub>cc</sub>   | V        |
| Operating Temperature    | T <sub>opr</sub> | <b>−40~85</b>   | °C       |
| Input Rise and Fall Time | dt/dv            | $0\sim100 \ (V_{CC} = 3.3 \pm 0.3 V)$<br>$0\sim20 \ (V_{CC} = 5 \pm 0.5 V)$ | ns / V   |

# DC ELECTRICAL CHARACTERISTICS

| PARAMETER SYMBOL              |                 | TEST CONDITION   |                                  | V <sub>CC</sub> | Ta = 25°C |            |                     | Ta = - 40~85°C      |                     | UNIT       |
|-------------------------------|-----------------|--|----------------------------------|-----------------|-----------|------------|---------------------|---------------------|---------------------|------------|
| PARAIVIETER                   | STIVIBUL        | TEST CONDITION   |                                  | (V)             | MIN.      | TYP.       | MAX.                | MIN.                | MAX.                | וואוט      |
| High - Level                  | .,              |  | 2.0<br>3.0~                      | 1.50            | _         | _          | 1.50                | _                   |                     |            |
| Input Voltage                 | V <sub>IH</sub> |  |                                  |                 |           | 1          | _                   | $V_{cc} \times 0.7$ | _                   | ٧          |
| Low - Level                   |                 |  |                                  | 2.0             | _         | -          | 0.50                | _                   | 0.50                |            |
| Input Voltage                 | V <sub>IL</sub> |  |                                  | 3.0~<br>5.5     | _         | _          | $V_{cc} \times 0.3$ | _                   | $V_{cc} \times 0.3$ | ٧          |
| Low - Level<br>Output Voltage |                 | V <sub>IN</sub> = V <sub>IH</sub>                          |                                  | 2.0             | _         | 0.0        | 0.1                 | _                   | 0.1                 |            |
|                               | V <sub>OL</sub> |  | $I_{OL} = 50 \mu A$              | 3.0<br>4.5      | _         | 0.0<br>0.0 | 0.1<br>0.1          | _                   | 0.1<br>0.1          | V          |
|                               |                 |  | $I_{OL} = 4mA$<br>$I_{OL} = 8mA$ | 3.0<br>4.5      | 1 1       | 1 1        | 0.36<br>0.36        | 1 1                 | 0.44<br>0.44        |            |
| Output<br>Off-State Current   | l <sub>oz</sub> | $V_{IN} = V_{IH}$ or $V_{IL}$<br>$V_{OUT} = V_{CC}$ or GND |                                  | 5.5             |           | ı          | ± 0.25              | 1                   | ± 2.50              |            |
| Input Leakage<br>Current      | I <sub>IN</sub> | V <sub>IN</sub> = 5.5V or GND                              |                                  | 0~5.5           | _         | . 1        | ±0.1                | _                   | ± 1.0               | μ <b>Α</b> |
| Quiescent Supply<br>Current   | I <sub>cc</sub> | $V_{IN} = V_{CC}$ or GND                                   |                                  | 5.5             | _         | _          | 2.0                 | _                   | 20.0                |            |

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Input Capacitance

**Output Capacitance** 

Power Dissipation Capacitance

| DADAMETED                | SYMBOL           | TEST CONDITION   |                        | Ta = 25°C           |      |      | $Ta = -40 \sim 85^{\circ}C$ |      | UNIT |      |
|--------------------------|------------------|------------------|------------------------|---------------------|------|------|-----------------------------|------|------|------|
| PARAMETER S              |                  |                  | V <sub>CC</sub> (V)    | C <sub>L</sub> (pF) | MIN. | TYP. | MAX.                        | MIN. | MAX. | UNIT |
| Propagation Delay Time   |                  | $R_L = 1k\Omega$ | 3.3 ± 0.3<br>5.0 ± 0.5 | 15                  | _    | 5.5  | 7.9                         | 1.0  | 9.5  | ns   |
|                          | <sup>t</sup> pZL |                  |                        | 50                  | _    | 8.0  | 11.4                        | 1.0  | 13.0 |      |
|                          |                  |                  |                        | 15                  | _    | 3.7  | 5.5                         | 1.0  | 6.5  |      |
|                          |                  |                  |                        | 50                  | _    | 5.2  | 7.5                         | 1.0  | 8.5  |      |
| Propagation Delay Time 1 | +                | D 1k∩            | 3.3 ± 0.3              | 50                  | _    | 8.0  | 11.4                        | 1.0  | 13.0 | nc   |
|                          | t <sub>pLZ</sub> | $R_L = 1k\Omega$ | 50+05                  | 50                  |      | 5.2  | 75                          | 1.0  | 2.5  | ns   |

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

(Note 1)

5.0 ± 0.5

50

5.2

4

5

6

7.5

10

1.0

8.5

10

рF

рF

рF

Average operating current can be obtained by the equation:

 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \text{ (per Gate)}$ 

CIN

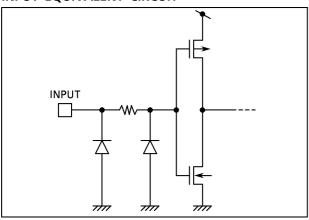
COUT

 $C_{PD}$ 

### NOISE CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

| PARAMETER                                       | SYMBOL           | TEST CONDIT           | Ta =                | LINIT |       |      |
|---|------------------|-----------------------|---------------------|-------|-------|------|
| PARAIVIETER                                     | 3 TIVIBOL        |                       | V <sub>CC</sub> (V) | TYP.  | LIMIT | UNIT |
| Quiet Output<br>Maximum Dynamic V <sub>OL</sub> | V <sub>OLP</sub> | C <sub>L</sub> = 50pF | 5.0                 | 0.3   | 0.8   | V    |
| Quiet Output<br>Minimum Dynamic V <sub>OL</sub> | V <sub>OLV</sub> | C <sub>L</sub> = 50pF | 5.0                 | -0.3  | -0.8  | V    |
| Minimum High Level<br>Dynamic Input Voltage     | V <sub>IHD</sub> | C <sub>L</sub> = 50pF | 5.0                 | _     | 3.5   | V    |
| Maximum Low Level<br>Dynamic Input Voltage      | V <sub>ILD</sub> | C <sub>L</sub> = 50pF | 5.0                 | _     | 1.5   | V    |

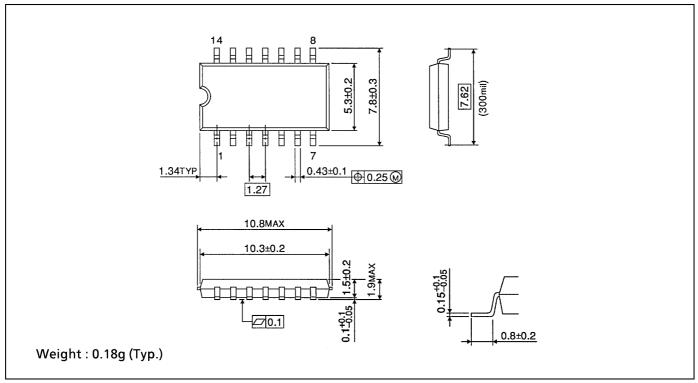
### INPUT EQUIVALENT CIRCUIT



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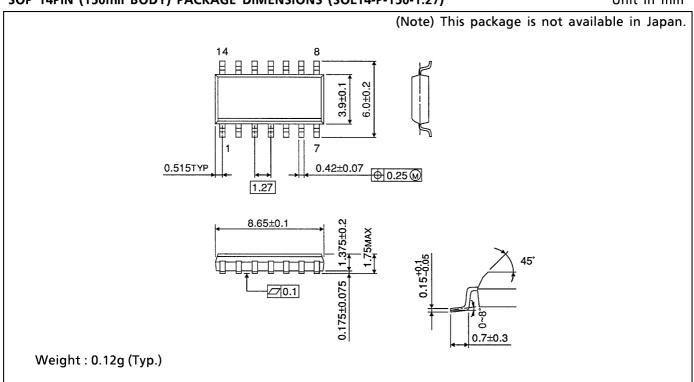
# SOP 14PIN (200mil BODY) PACKAGE DIMENSIONS (SOP14-P-300-1.27)

Unit in mm



# SOP 14PIN (150mil BODY) PACKAGE DIMENSIONS (SOL14-P-150-1.27)

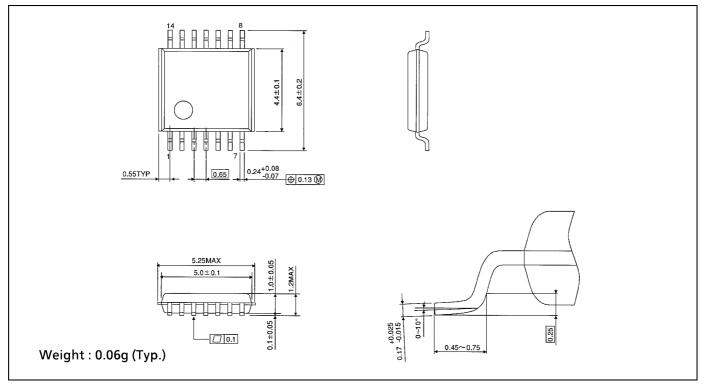
Unit in mm



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# TSSOP 14PIN PACKAGE DIMENSIONS (TSSOP14-P-0044-0.65)

Unit in mm



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